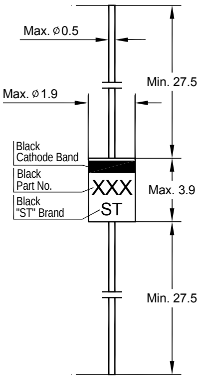
1N4150

Silicon Epitaxial Planar Switching Diode

for general purpose switching applications

Features

- Fast switching speed
- High reliability



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	50	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Power Dissipation	P_{tot}	500 1)	mW
Junction Temperature	T_j	200	°C
Operating and Storage Temperature Range	T_{stg}	- 65 to + 175	°C

1) Valid provided that leads are at a distance of 8 mm from case kept at ambient temperature

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 200 mA	V_F	1.2	V
Reverse Current at V_R = 50 V	I_R	100	nA
Reverse Recovery Time at $I_F = I_R$ = 200 mA, $I_{rr} = 0.1 \times I_R$, R_L = 100 Ω	t_{rr}	4	ns